

# 2SK3026 (Tentative)

Silicon N-Channel Power F-MOS FET

## ■ Features

- Avalanche energy capacity guaranteed
  - High-speed switching
  - Low ON-resistance
  - No secondary breakdown
  - Low-voltage drive
  - High electrostatic breakdown voltage

## ■ Applications

- Contactless relay
  - Diving circuit for a solenoid
  - Driving circuit for a motor
  - Control equipment
  - Switching power supply

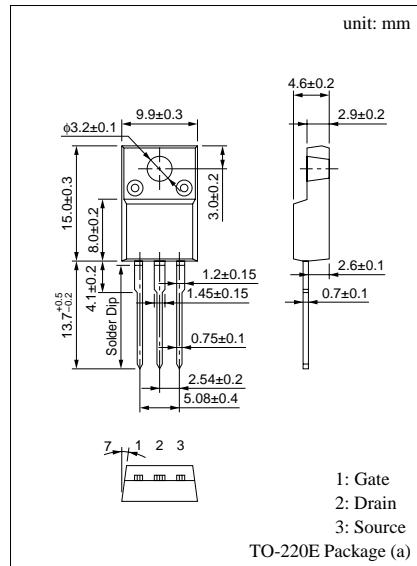
#### ■ Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ )

Parameter		Symbol	Ratings	Unit
Drain to Source breakdown voltage		V <sub>DSS</sub>	60	V
Gate to Source voltage		V <sub>GSS</sub>	±20	V
Drain current	DC	I <sub>D</sub>	±40	A
	Pulse	I <sub>DP</sub>	±80	A
Avalanche energy capacity		EAS*	80	mJ
Allowable power dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	50	W
	T <sub>a</sub> = 25°C		2	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to +150	°C

\* L = 0.1mH, I<sub>L</sub> = 40A, 1 pulse

### ■ Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0			10	µA
Gate to Source leakage current	I <sub>GS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0			±10	µA
Drain to Source breakdown voltage	V <sub>DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	60			V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1		2.5	V
Drain to Source ON-resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A		12	18	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = 4V, I <sub>D</sub> = 20A		16	24	mΩ
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 20A	19	37		S
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 20A, V <sub>GS</sub> = 0			-1.2	V
Input capacitance (Common Source)	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz		2350		pF
Output capacitance (Common Source)	C <sub>oss</sub>			810		pF
Reverse transfer capacitance (Common Source)	C <sub>rss</sub>			450		pF
Turn-on time (delay time)	t <sub>d(on)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> = 20A V <sub>GS</sub> = 10V, R <sub>L</sub> = 1.5Ω		15		ns
Rise time	t <sub>r</sub>			55		ns
Fall time	t <sub>f</sub>			180		ns
Turn-off time (delay time)	t <sub>d(off)</sub>			600		ns
Thermal resistance between channel and case	R <sub>th(ch-c)</sub>				2.5	°C/W
Thermal resistance between channel and atmosphere	R <sub>th(ch-a)</sub>				62.5	°C/W



## Internal Connection

